

**In the Specification:**

Please amend Paragraph 14 as follows:

In FIG. 1B a first dielectric layer 105 having a thickness T1 is formed on a top surface 110 of substrate 100. In the present example, dielectric layer 105 is ~~silicon~~ silicon oxide ( $\text{SiO}_2$ ) formed by a rapid thermal oxidation (RTO) process and T1 is about 50 to 100. The purpose of dielectric layer 105 is to provide an amorphous screen dielectric (in the present example  $\text{SiO}_2$ ) to prevent channeling of the implanted species through the crystal planes of substrate 100 during introduction of interfacial species as describe infra. In the present example, first dielectric layer 105 may be considered a sacrificial layer.